

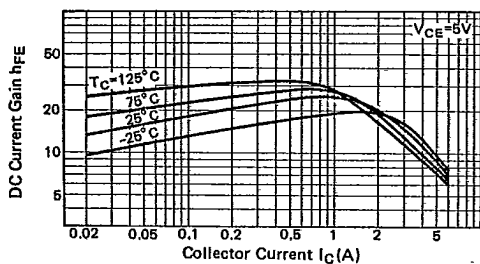
FUJITSU

Silicon High Speed Power Transistor

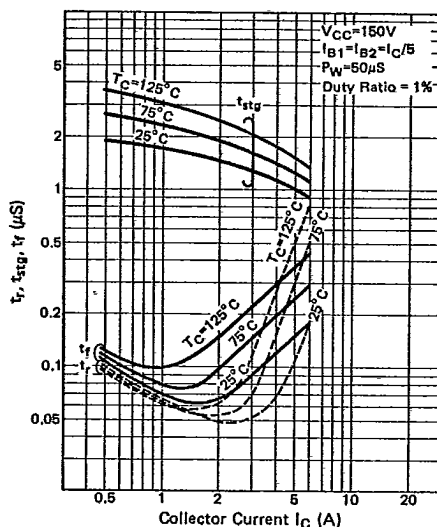
1-69

2SC3056, 2SC3056A

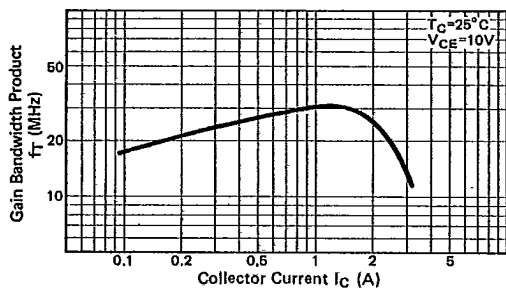
DC CURRENT GAIN



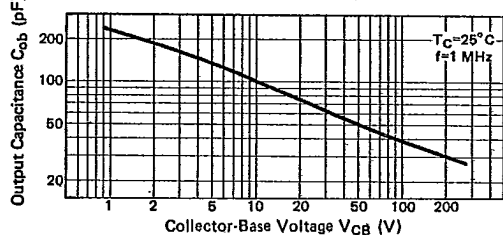
SWITCHING TIME



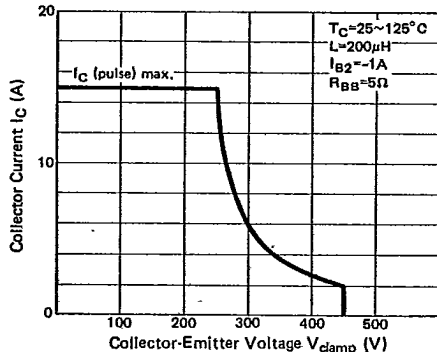
GAIN BANDWIDTH PRODUCT



OUTPUT CAPACITANCE



REVERSE BIAS SAFE OPERATING AREA

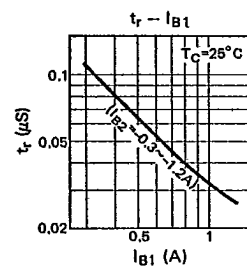
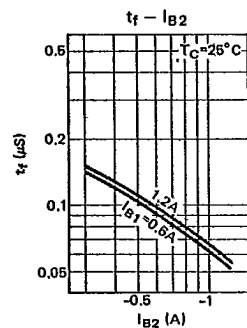
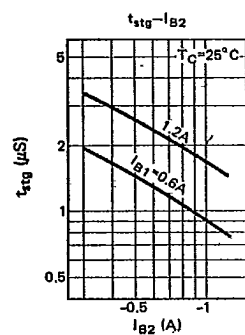


2SC3056, 2SC3056A

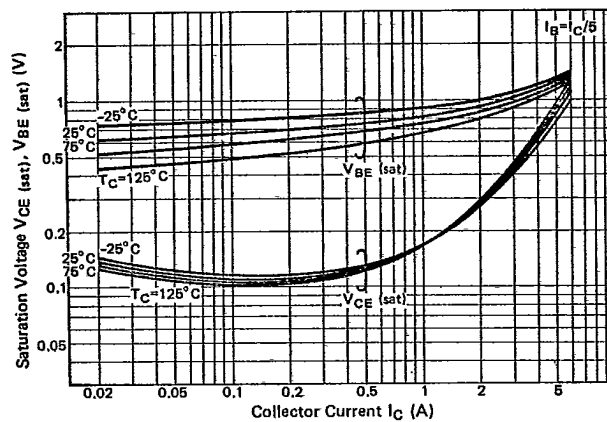
SWITCHING TIME

 $V_{CC}=150V$ $I_C=5A$ $P_W=50\mu S$

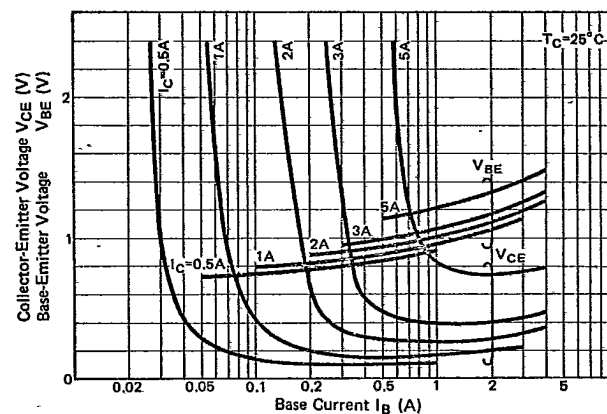
Duty Ratio = 1%



SATURATION VOLTAGE

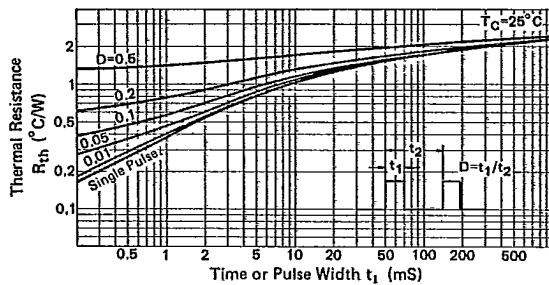
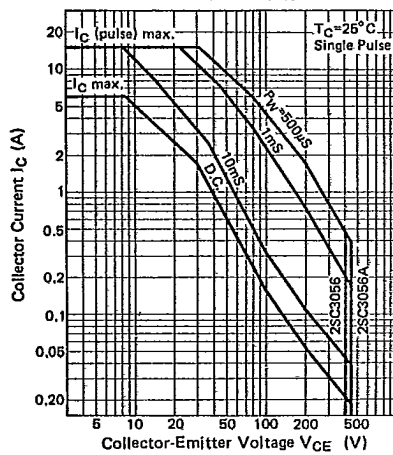
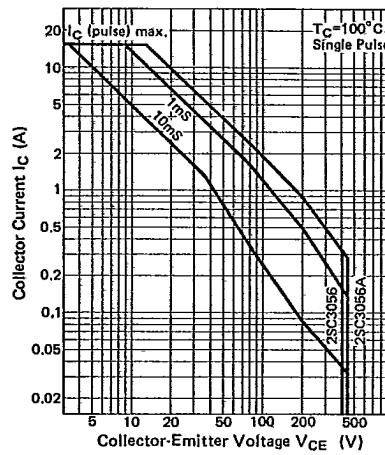


COLLECTOR SATURATION REGION



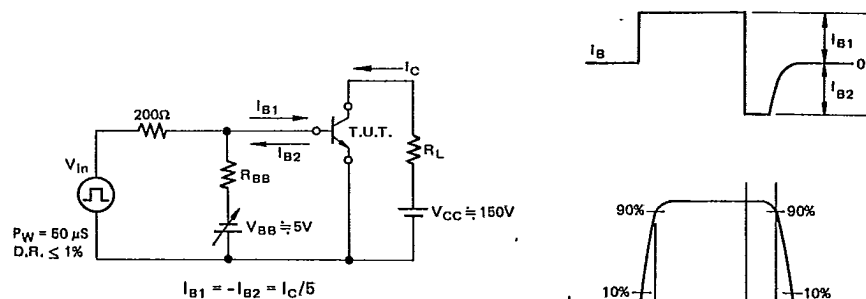
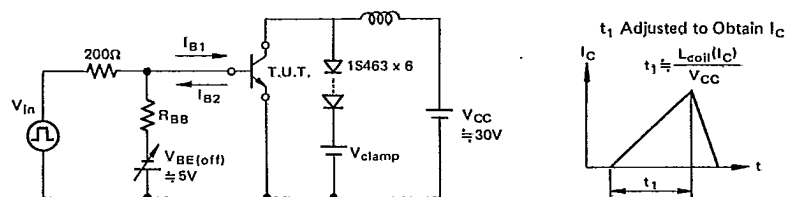
2SC3056, 2SC3056A

THERMAL RESPONSE

FORWARD BIAS SAFE
OPERATING AREAFORWARD BIAS SAFE
OPERATING AREA

2SC3056, 2SC3056A

TEST CIRCUIT USED FOR MEASUREMENT OF SWITCHING TIME (RESISTIVE)


TEST CIRCUIT USED FOR MEASUREMENT OF $V_{CEX(SUS)}$ AND REVERSE BIAS SAFE OPERATING AREA


(a) $V_{CEX(SUS)}$
 $I_C = 2A, I_{B1} = 1A, I_{B2} = -1A, R_{BB} = 5\Omega, V_{clamp} = 450V$

(b) Reverse Bias Safe Operating Area
 $I_{B1} \leq 4A, I_{B2} = -1A, R_{BB} = 5\Omega$